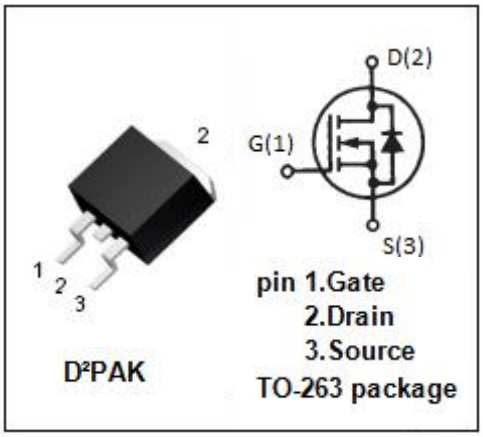
isc N-Channel MOSFET Transistor IXTA8N65X2

- **FEATURES**
- Drain Source Voltage-
  : V_{DSS}= 650V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ ≤500mΩ @V_{GS}= 10V
- Fast Switching
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



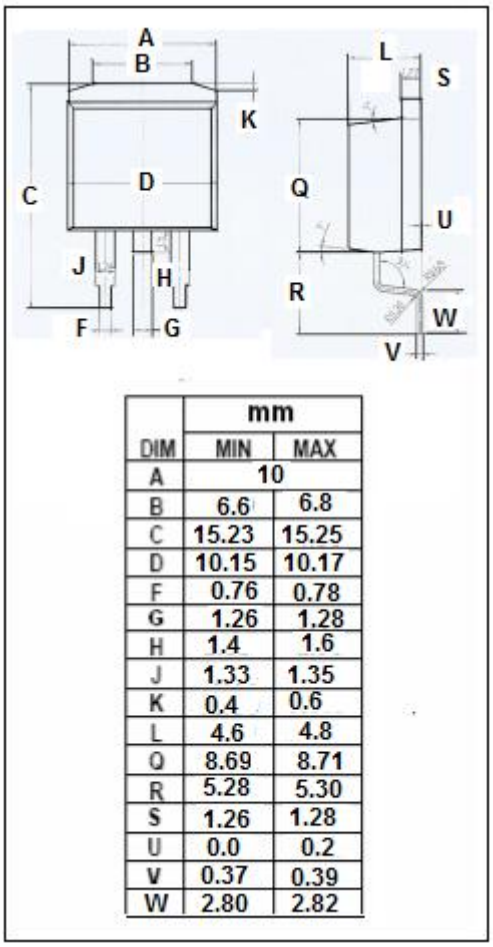
- **APPLICATIONS**
- Easy to Mount
- Space Savings
- High Power Density

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage-Continuous	±30	V
I_D	Drain Current-Continuous	8	A
I_{DM}	Drain Current-Single Plused	16	A
P_D	Total Dissipation @T_C=25℃	150	W
T_j	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	0.83	℃/W



DIM	mm MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

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• ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 250uA	650			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 250uA	3		5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 4A			500	mΩ
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±30V;V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 600V; V_{GS}= 0 V_{DS}= 600V; V_{GS}= 0;T_J=125℃			10 150	μA
V_{SD}	Diode Forward On-voltage	I_F= 8A ;V_{GS}= 0			1.4	V